



#### LOW NOISE, LOW POWER, 1MHZ, RRIO SINGLE / DUAL CMOS OPERATIONAL AMPLIFIERS

## Description

The DIODES AS348/AS2348 are single/dual channels RRIO amplifiers (rail-to-rail input and output), which provide not only maximum output-voltage swing capability but also an extended 300mV common-mode voltage beyond the supply rail. The devices are fully specified to operate from 1.6V to 5.5V single-supply, or ±0.8V and ±2.5V dual-supply applications.

The devices feature a good speed/power consumption ratio, offering 1MHz gain bandwidth while consuming 70µA per channel (typ). They are unity-gain stable for capacitive loads up to 100pF. The low noise density 27nV/ $\sqrt{Hz}$ , low input offset voltage 0.5mV and low input offset drift 2µV/°C make them ideal for applications that require precision. With the input bias current is 1pA at room temperature, it is well suitable for low-voltage, low-noise, and low-power applications.

The AS348/AS2348 offer industry-standard packages. The AS348 is available in the SOT25 package, and the AS2348 is offered in the MSOP-8 and SO-8 packages. Temperature is specified for operation: from -40°C to +125°C among all supply voltages. The wide temperature ranges and high ESD tolerance facilitate their use in harsh applications.

## **Features**

- Single-Supply Voltage Range: 1.6V to 5.5V
- Dual-Supply Voltage Range: ±0.8V to ±2.5V
- Ultra-Low Input Bias Current: 1pA (typ)
- Offset Voltage: 0.5mV (typ), 2.5mV (max)
- Low Input Offset Drift: 2µV/°C (typ)
- Rail-to-Rail Input
  V<sub>CM</sub>: 300mV Beyond Supply Rail @ V<sub>CC</sub> = 3V or 5V
  Rail-to-Rail Output Swing:
  10kΩ Load: 4mV from Rail
  1kΩ Load: 25mV from Rail
- Supply Current: 70µA/Channel (typ)
- Unity-Gain Stable up to 100pF Capacitive Load Gain Bandwidth: 1.0MHz
- Slew Rate: 0.45V/µs @ Vcc = 5.0V
- Operation Ambient Temperature Range: -40°C to +125°C
- ESD Protection JESD 22, 4000V HBM (A114)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/guality/product-definitions/</u>

## **Pin Assignments**



SO-8/MSOP-8 (AS2348)

## Applications

- Active filters
- Sensors interfaces
- Photodiode amplification
- Smoke alarms, CO detectors
- Battery-powered applications
- Portable equipment
- Medical instrumentation
- Pulse blood oximeters, glucose meters

- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



## **Functional Block Diagram**



Block Diagram of AS2348



## Absolute Maximum Ratings (Note 4)

Symbol	Parameter	Rat	ing	Unit	
Vcc	Power-Supply Voltage	6.	6.0		
VID	Differential Input Voltage	6.	0	V	
Vin	Input Voltage	-0.3 to \	/cc+0.5	V	
TJ	Operating Junction Temperature	+1:	+150		
		SOT25	220		
θ」Α	Thermal Resistance (Junction to Ambient)	SO-8	150	°C/W	
		MSOP-8	200		
T <sub>STG</sub>	Storage Temperature Range	-65 to	+150	°C	
T <sub>LEAD</sub>	Lead Temperature (Soldering, 10 Seconds)	Lead Temperature (Soldering, 10 Seconds) +260			
_	ESD (Human Body Model)	ESD (Human Body Model) ±4000			
	ESD (Machine Model)	ESD (Machine Model) ±300			

Note 4: Stresses greater than those listed under "Absolute Maximum Ratings" can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods can affect device reliability.

## **Recommended Operating Conditions**

Symbol	Parameter	Min	Мах	Unit
Vcc	Supply Voltage	1.6	5.5	V
T <sub>A</sub>	Operating Ambient Temperature Range	-40	+125	°C



## **Electrical Characteristics**

Symbol	Param	eter	Conditions	Min	Тур	Мах	Unit
Vos	Input Offset Voltage		_	_	0.5	2.5	mV
Ів	Input Bias Current		_	_	1.0	—	pА
los	Input Offset Current		_	_	1.0	_	pА
V <sub>CM</sub>	Input Common-Mod	e Voltage Range	_	-0.2	_	1.8	V
CMRR	Common-Mode Reje	ection Ratio	V <sub>CM</sub> = -0.2V to 1.8V	55	75	_	dB
Gv	Large Signal Voltage Gain		$R_L = 10k\Omega \text{ to } V_{CC}/2,$ $V_{OUT} = 0.2V \text{ to } 1.4V$	90	110	_	dB
ΔVos/ΔT	Input Offset Voltage Drift		_	_	2.0	_	µV/°C
		( <b>D</b> "	$R_L = 1k\Omega$ to $V_{CC}/2$	_	30	50	
Vol/Voh	Output-Voltage Swir	ng from Rail	$R_L = 10k\Omega$ to $V_{CC}/2$	_	3	15	mV
Isink		Sink	Vout = Vcc	8	10	_	
ISOURCE	Output Current	Source	Vout = 0V	5	8.5	_	mA
Ζουτ	Closed-Loop Output Impedance		f = 10kHz, A∨ = 1	_	9	_	Ω
PSRR	Power-Supply Rejection Ratio		V <sub>CC</sub> = 1.6V to 5.0V	66	80	_	dB
lcc	Supply Current (Per	Amplifier)	Vout = Vcc/2, lout = 0	_	70	90	μA

1.6V DC Electrical Characteristics (V<sub>CC</sub> = 1.6V, V<sub>EE</sub> = 0, V<sub>OUT</sub> = V<sub>CC</sub>/2, V<sub>CM</sub> = V<sub>CC</sub>/2, T<sub>A</sub> = +25°C, unless otherwise specified.)

**1.6V AC Electrical Characteristics** ( $V_{CC} = 1.6V$ ,  $V_{EE} = 0$ ,  $V_{OUT} = V_{CC}/2$ ,  $V_{CM} = V_{CC}/2$ ,  $T_A = +25^{\circ}C$ , unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
GBP	Gain Bandwidth Product	C <sub>L</sub> = 100pF	_	1.0	_	MHz
SR	Slew Rate (Note 5)	1V Step, CL = 100pF, RL = 10kΩ	_	0.32	_	V/µs
фм	Phase Margin	R <sub>L</sub> = 100kΩ	_	67	_	Degrees
THD+N	Total Harmonic Distortion+Noise	$\label{eq:f} \begin{split} f &= 1 kHz, \ A_V = 1, \ V_{IN} = 1 V_{PP}, \\ R_L &= 10 k\Omega, \ C_L = 100 pF \end{split}$	_	-70	_	dB
en	Voltage Noise Density	f = 1kHz	_	27	_	$nV/\sqrt{Hz}$



## Electrical Characteristics (continued)

Symbol	Param	eter	Conditions	Min	Тур	Max	Unit
V <sub>OS</sub>	Input Offset Voltage		_	—	0.5	2.5	mV
lB	Input Bias Current		_	—	1.0	—	pА
los	Input Offset Current		_	—	1.0	—	pА
Vсм	Input Common-Mod	e Voltage Range	_	-0.2	_	2.0	V
CMRR	Common-Mode Reje	ection Ratio	V <sub>CM</sub> = -0.2V to 2.0V	55	75	_	dB
Gv	Large Signal Voltage Gain		$\label{eq:RL} \begin{split} R_L &= 10 k \Omega \text{ to } V_{CC}/2, \\ V_{OUT} &= 0.2 V \text{ to } 1.6 V \end{split}$	90	112	_	dB
ΔV <sub>OS</sub> /ΔT	Input Offset Voltage Drift		_	—	2.0	—	µV/°C
			$R_L = 1k\Omega$ to $V_{CC}/2$	—	25	50	
V <sub>OL</sub> /V <sub>OH</sub>	Output-Voltage Swir	ng from Rail	$R_L = 10k\Omega$ to $V_{CC}/2$	_	3	15	mV
Isink		Sink	Vout = Vcc	12	16	_	
ISOURCE	Output Current	Source	Vout = 0V	10	14	_	mA
Z <sub>OUT</sub>	Closed-Loop Output Impedance		f = 10kHz	_	9	_	Ω
PSRR	Power-Supply Rejection Ratio		V <sub>CC</sub> = 1.6V to 5.0V	66	80	_	dB
lcc	Supply Current (Per	Amplifier)	Vout = Vcc/2, Iout = 0	—	70	90	μA

**1.8V DC Electrical Characteristics** ( $V_{CC} = 1.8V$ ,  $V_{EE} = 0$ ,  $V_{OUT} = V_{CC}/2$ ,  $V_{CM} = V_{CC}/2$ ,  $T_A = +25^{\circ}C$ , unless otherwise specified.)

#### 1.8V AC Electrical Characteristics (Vcc = 1.8V, VEE = 0, Vour = Vcc/2, Vcm = Vcc/2, TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
GBP	Gain Bandwidth Product	C <sub>L</sub> = 100pF	_	1.0		MHz
SR	Slew Rate (Note 5)	1V Step, C <sub>L</sub> = 100pF, R <sub>L</sub> = 10kΩ		0.34		V/µs
Фм	Phase Margin	R <sub>L</sub> = 100kΩ		67		Degrees
THD+N	Total Harmonic Distortion+Noise	f = 1kHz, A <sub>V</sub> = 1, V <sub>IN</sub> = 1V <sub>PP</sub> , R <sub>L</sub> = 10kΩ, C <sub>L</sub> = 100pF	_	-70	_	dB
en	Voltage Noise Density	f = 1kHz	_	27		$nV/\sqrt{Hz}$



## Electrical Characteristics (continued)

Symbol	Param	eter	Conditions	Min	Тур	Мах	Unit
Vos	Input Offset Voltage		_	_	0.5	2.5	mV
lв	Input Bias Current		_	—	1.0	—	pА
los	Input Offset Current		_	_	1.0		pА
Vсм	Input Common-Mod	e Voltage Range	_	-0.3		3.3	V
			V <sub>CM</sub> = -0.3V to 1.8V	62	80	_	
CMRR	Common-Mode Rejection Ratio		V <sub>CM</sub> = -0.3V to 3.3V	58	75		dB
_	Large Signal Voltage Gain		$R_L = 1k\Omega$ to $V_{CC}/2$ , $V_{OUT} = 0.2V$ to 2.8V	90	110	_	
Gv			$R_{L} = 10k\Omega \text{ to } V_{CC}/2,$ $V_{OUT} = 0.1V \text{ to } 2.9V$	95	115		dB
ΔVos/ΔT	Input Offset Voltage	Drift	_	_	2.0	_	μV/°C
			$R_L = 1k\Omega$ to $V_{CC}/2$	_	20	50	
Vol/Voн	Output-Voltage Swir	ng from Rail	$R_L = 10k\Omega$ to $V_{CC}/2$	_	3	15	mV
Isink		Sink	V <sub>OUT</sub> = V <sub>CC</sub>	50	60	_	_
ISOURCE	Output Current	Source	Vout = 0V	50	65	_	mA
Zout	Closed-Loop Output Impedance		f = 10kHz	_	9	_	Ω
PSRR	Power-Supply Reject	tion Ratio	V <sub>CC</sub> = 1.6V to 5.0V	66	80	_	dB
Icc	Supply Current (Per	Amplifier)	Vout = Vcc/2, lout = 0	—	70	90	μA

3.0V DC Electrical Characteristics ( $V_{CC} = 3.0V$ ,  $V_{EE} = 0$ ,  $V_{OUT} = V_{CC}/2$ ,  $V_{CM} = V_{CC}/2$ ,  $T_A = +25^{\circ}C$ , unless otherwise specified.)

## 3.0V AC Electrical Characteristics ( $V_{CC} = 3.0V$ , $V_{EE} = 0$ , $V_{OUT} = V_{CC}/2$ , $V_{CM} = V_{CC}/2$ , $T_A = +25^{\circ}C$ , unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
GBP	Gain Bandwidth Product	C <sub>L</sub> = 100pF	—	1.0	-	MHz
SR	Slew Rate (Note 5)	G = 1, 2V Step, $C_L = 100 pF, R_L = 10 k\Omega$	_	0.40		V/µs
ФМ	Phase Margin	$R_L = 100 k\Omega$	—	67	-	Degrees
THD+N	Total Harmonic Distortion+Noise	$f = 1 kHz, G = 1, V_{IN} = 1 V_{PP},$ $R_L = 10 k\Omega, C_L = 100 pF$	_	-70		dB
en	Voltage Noise Density	f = 1kHz	_	27		$nV/\sqrt{Hz}$



## Electrical Characteristics (continued)

Symbol	Param	eter	Conditions	Min	Тур	Мах	Unit
Vos	Input Offset Voltage		_	_	0.5	2.5	mV
lв	Input Bias Current		_	_	1.0		pА
los	Input Offset Current		_	_	1.0		pА
Vсм	Input Common-Mod	e Voltage Range	_	-0.3		5.3	V
			V <sub>CM</sub> = -0.3V to 3.8V	70	85	_	
CMRR	Common-Mode Rejection Ratio		V <sub>CM</sub> = -0.3V to 5.3V	65	90		dB
			$R_L = 1k\Omega$ to V <sub>CC</sub> /2, V <sub>OUT</sub> = 0.2V to 4.8V	80	92	_	
Gv	Gv Large Signal Voltage Gain	e Gain	$R_{L} = 10k\Omega \text{ to } V_{CC}/2,$ $V_{OUT} = 0.05V \text{ to } 4.95V$	85	98		dB
ΔVos/ΔT	Input Offset Voltage	Drift	_	_	2.0	_	μV/°C
			$R_L = 1k\Omega$ to V <sub>CC</sub> /2	_	25	50	
Vol/Voh	Output-Voltage Swir	ng from Rail	$R_L = 10k\Omega$ to $V_{CC}/2$	_	4	15	mV
Isink		Sink	V <sub>OUT</sub> = V <sub>CC</sub>	100	150	_	
ISOURCE	Output Current	Source	Vout = 0V	110	185	_	mA
_	Closed-Loop Output Impedance		f = 1kHz, Av = 1	_	9	_	Ω
PSRR	Power-Supply Reject	tion Ratio	Vcc = 1.6V to 5.0V	66	80	_	dB
Icc	Supply Current (Per	Amplifier)	Vout = Vcc/2, lout = 0	—	70	90	μA

5.0V DC Electrical Characteristics ( $V_{CC} = 5.0V$ ,  $V_{EE} = 0$ ,  $V_{OUT} = V_{CC}/2$ ,  $V_{CM} = V_{CC}/2$ ,  $T_A = +25^{\circ}C$ , unless otherwise specified.)

5.0V AC Electrical Characteristics ( $V_{CC} = 5.0V$ ,  $V_{EE} = 0$ ,  $V_{OUT} = V_{CC}/2$ ,  $V_{CM} = V_{CC}/2$ ,  $T_A = +25^{\circ}C$ , unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
GBP	Gain Bandwidth Product	C <sub>L</sub> = 100pF		1.0	—	MHz
SR	Slew Rate (Note 5)	2V Step, C <sub>L</sub> = 100pF, R <sub>L</sub> = 10kΩ	_	0.45	_	V/µs
Фм	Phase Margin	$R_L = 100k\Omega$	—	67	—	Degrees
THD+N	THD+N	$\label{eq:f} \begin{split} f &= 1 kHz,  A_V = 1,  V_{IN} = 1 V_{PP}, \\ R_L &= 10 k\Omega,  C_L = 100 pF \end{split}$	_	-70	_	dB
en	Voltage Noise Density	f = 1kHz	_	27	_	$nV/\sqrt{Hz}$



## **Performance Characteristics**



Input Offset Voltage vs. Input Common Mode Voltage



#### Input Offset Voltage vs. Input Common Mode Voltage



250 Supply Current (µA) 120 100 200 T.=85°C .  $=25^{\circ}C$ \_ F + - $T = -40^{\circ}C$ **Dual Amplifiers** 50 V<sub>out</sub>=V<sub>cc</sub>/2 I<sub>out</sub>=0mA 1 0 1.5 2.0 2.5 3.0 3.5 4.0 4.5 5.0 5.5 Supply Voltage (V)

#### Supply Current vs. Supply Voltage





#### Input Offset Voltage vs. Input Common Mode Voltage





### Output Voltage vs. Output Current



**Output Voltage vs. Output Current** 



**Output Short Circuit Current vs. Temperature** 



**Output Voltage vs. Output Current** 



**Output Voltage vs. Output Current** 



**Output Short Circuit Current vs. Temperature** 







Output Short Circuit Current vs. Supply Voltage

**Output Voltage Swing vs. Supply Voltage** 



**Output Voltage Swing vs. Temperature** 





**Output Voltage Swing vs. Supply Voltage** 



**Output Voltage Swing vs. Temperature** 















Gain and Phase vs. Frequency with Capacitive Load



Gain and Phase vs. Frequency with Resistive Load



Gain and Phase vs. Frequency with Capacitive Load



AS348/AS2348 Document number: DS45094 Rev. 1 - 2







Gain and Phase vs. Frequency







Gain and Phase vs. Frequency



Gain and Phase vs. Frequency with Resistive Load



#### Gain and Phase vs. Frequency with Capacitive Load



AS348/AS2348 Document number: DS45094 Rev. 1 - 2





#### **Output Impedance vs. Frequency**

THD+N vs. Output Voltage



THD+N vs. Frequency



**Small Signal Pulse Response** 



Time (2µs/div)

Input Voltage Noise Density



#### Small Signal Pulse Response



Time (2µs/div)





#### **Small Signal Pulse Response**







#### **Small Signal Pulse Response**



Time (2µs/div)







VIN

V<sub>OUT</sub> 1V/div

1V/div

## Performance Characteristics (continued)



Large Signal Pulse Response

 $C_L = 200 pF, R_L = 10 k\Omega, A_V = 1$ 

Time (10µs/div)

10.0µs

 $V_{CC} = 3.0V$  $V_{EE} = 0V$ 

2.50G次/抄 ① J 2.80



#### Large Signal Pulse Response









No Phase Reversal V<sub>IN</sub>  $V_{CC} = 2.5V$  $V_{EE} = -2.5V$  $V_{IN}$ 1V/div Vout Vout 1V/div  $f = 1 \text{kHz}, R_L = 10 \text{k}\Omega, V_{IN} = 6 V_{PP}, A_V = 1$ 2.586278 B J-20.

Time (200µs/div)

AS348/AS2348 Document number: DS45094 Rev. 1 - 2





AS348/AS2348 Document number: DS45094 Rev. 1 - 2



## **Ordering Information**



Part Number	Package Code	Baakaga	Packin	g
Fait Nulliper	Fackage Code	Package	Qty.	Carrier
AS348W5-7	W5	SOT25	3,000	7" Tape and Reel
AS2348S-13	S	SO-8	4,000	13" Tape and Reel
AS2348M8-13	M8	MSOP-8	3,000	13" Tape and Reel

## **Marking Information**

(1) SOT25



Part Numb	er	Package	Identification Code
AS348W5	7	SOT25	PH

(2) SO-8

#### (Top View) 7 6 5 8 DH YY: Year: 23, 24, 25~ AS2348 WW: Week: 01~52; 52 represents 52 and 53 week <u>YY WW XX</u> XX: Internal Code 0 1 2 3 4

Part Number	Part Number Package	
AS2348S-13	SO-8	AS2348



#### (3) MSOP-8



<u>YY</u> : Year : 23, 24, 25~ <u>WW</u> : Week : 01~52; 52 represents 52 and 53 week <u>XX</u> : Internal Code

Part Number	Package	Identification Code
AS2348M8-13	MSOP-8	AS2348

## Package Outline Dimensions (All dimensions in mm(inch).)

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### (1) Package Type: SOT25





## Package Outline Dimensions (All dimensions in mm(inch).) (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### (2) Package Type: SO-8



Note: Eject hole, oriented hole and mold mark is optional.



0.750(0.030) 0.970(0.038)

0.800(0.031) 1.200(0.047)

## Package Outline Dimensions (All dimensions in mm(inch).) (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### (3) Package Type: MSOP-8



Note: Eject hole, oriented hole and mold mark is optional.



# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

## (1) Package Type: SOT25



Dimensions	Z	G	X	Y	E1	E2
	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	3.600/0.142	1.600/0.063	0.700/0.028	1.000/0.039	0.950/0.037	1.900/0.075



## Suggested Pad Layout (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### (2) Package Type: SO-8



Dimensions	Z	G	X	Y	E
	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	6.900/0.272	3.900/0.154	0.650/0.026	1.500/0.059	1.270/0.050



## Suggested Pad Layout (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### (3) Package Type: MSOP-8



Dimensions	Z	G	X	Y	E
	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	5.500/0.217	2.800/0.110	0.450/0.018	1.350/0.053	0.650/0.026

## **Mechanical Data**

#### SOT25

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.015 grams (Approximate)

#### SO-8

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (Approximate)

#### MSOP-8

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 3
- Weight: 0.0246 grams (Approximate)



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